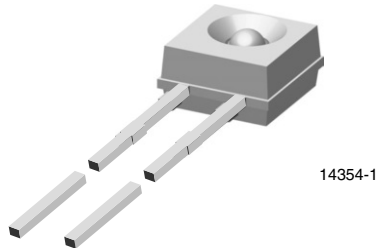


Infrared Emitting Diode, RoHS Compliant, 950 nm, GaAs



DESCRIPTION

The TSKS5400-FSZ is an infrared, 950 nm emitting diode in GaAs technology with high radiant power, molded in a clear plastic package.

FEATURES

- Package type: leaded
- Package form: side view lens
- Dimensions (L x W x H in mm): 5 x 2.65 x 5
- Peak wavelength: $\lambda_p = 950$ nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: $\varphi = \pm 30^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Package matched with detector TEKS5400
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC


RoHS
COMPLIANT

APPLICATIONS

- Photointerrupters
- Transmissive sensors, gap sensors
- Reflective sensors

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	φ (deg)	λ_p (nm)	t_r (ns)
TSKS5400-FSZ	4.5	± 30	950	800

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSKS5400-FSZ	Tape and ammpack	MOQ: 2000 pcs, 2000 pcs/ammopack	Side view lens

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	6	V
Forward current		I_F	100	mA
Surge forward current	$t_p \leq 100 \mu\text{s}$	I_{FSM}	2	A
Power dissipation		P_V	170	mW
Junction temperature		T_j	100	$^\circ\text{C}$
Operating temperature range		T_{amb}	- 25 to + 85	$^\circ\text{C}$
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ\text{C}$
Soldering temperature	$t \leq 5$ s, 2 mm from case	T_{sd}	260	$^\circ\text{C}$
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R_{thJA}	270	K/W

Note

$T_{amb} = 25$ $^\circ\text{C}$, unless otherwise specified

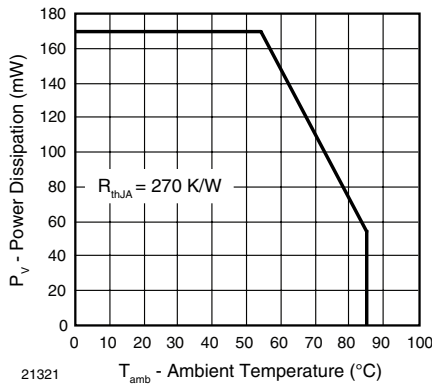


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

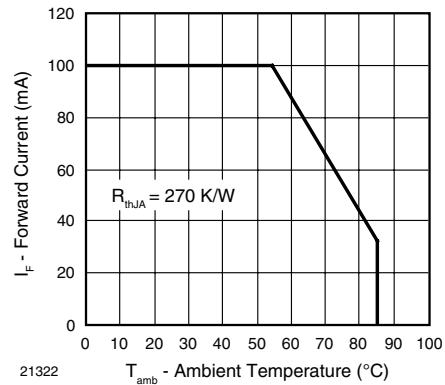


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100 \text{ mA}$, $t_p \leq 20 \text{ ms}$	V_F		1.3	1.7	V
Reverse voltage	$I_R = 10 \text{ }\mu\text{A}$	V_R	6			V
Temperature coefficient of V_F	$I_F = 100 \text{ mA}$	TK_{V_F}		- 1.3		mV/K
Junction capacitance	$V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$, $E = 0$	C_j		30		pF
Radiant intensity	$I_F = 100 \text{ mA}$, $t_p \leq 20 \text{ ms}$	I_e	2	4.5	7	mW/sr
Radiant power	$I_F = 50 \text{ mA}$, $t_p \leq 20 \text{ ms}$	ϕ_e		10		mW
Temperature coefficient of ϕ_e	$I_F = 50 \text{ mA}$	TK_{ϕ_e}		- 0.8		%/K
Angle of half sensitivity		ϕ		± 30		deg
Peak wavelength	$I_F = 50 \text{ mA}$	λ_p		950		nm
Spectral bandwidth	$I_F = 50 \text{ mA}$	$\Delta\lambda$		50		nm
Rise time	$I_F = 100 \text{ mA}$	t_r		800		ns
	$I_F = 1 \text{ A}$, $t_p/T = 0.01$, $t_p \leq 10 \text{ }\mu\text{s}$	t_r		450		ns

Note

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

BASIC CHARACTERISTICS

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

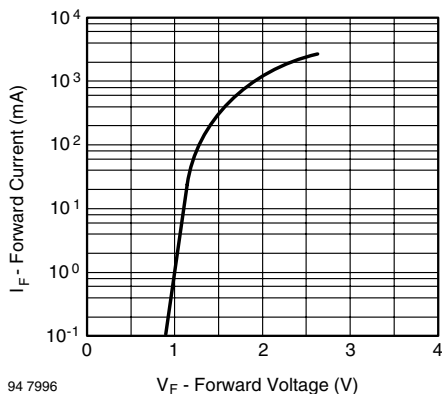


Fig. 3 - Pulse Forward Current vs. Forward Voltage

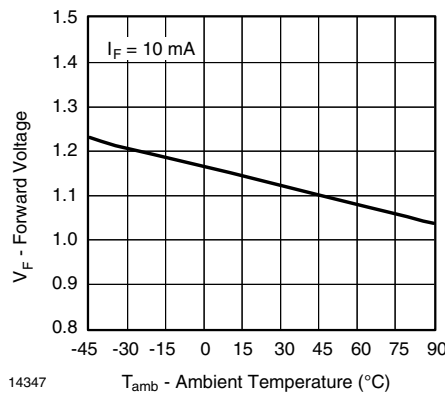


Fig. 4 - Forward Voltage vs. Ambient Temperature

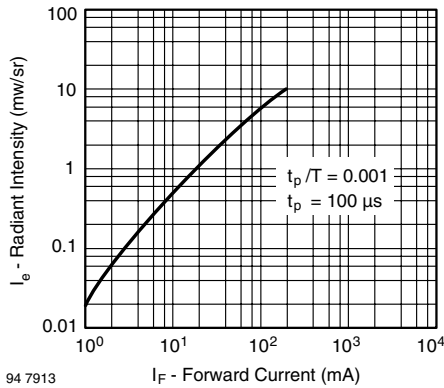


Fig. 5 - Radiant Intensity vs. Forward Current

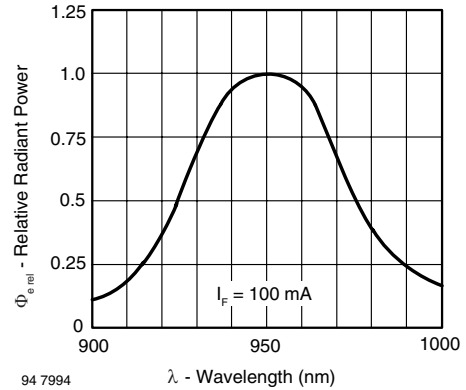


Fig. 8 - Relative Radiant Power vs. Wavelength

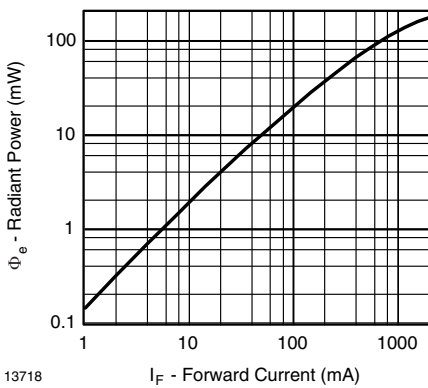


Fig. 6 - Radiant Power vs. Forward Current

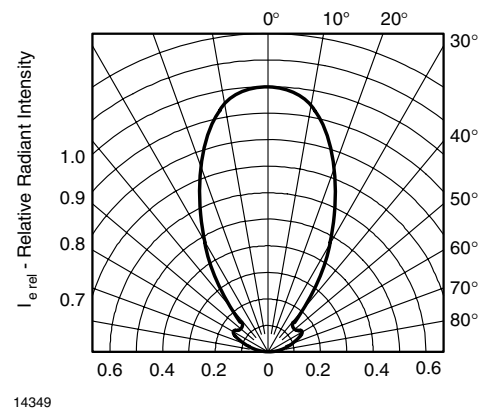


Fig. 9 - Relative Radiant Intensity vs. Angular Displacement

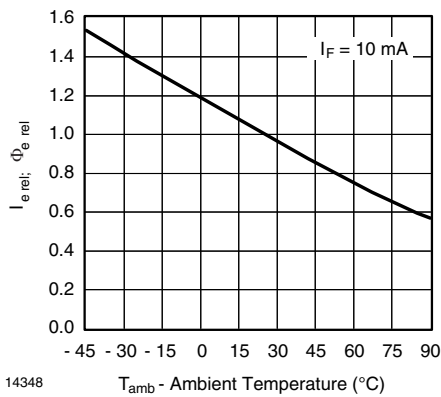


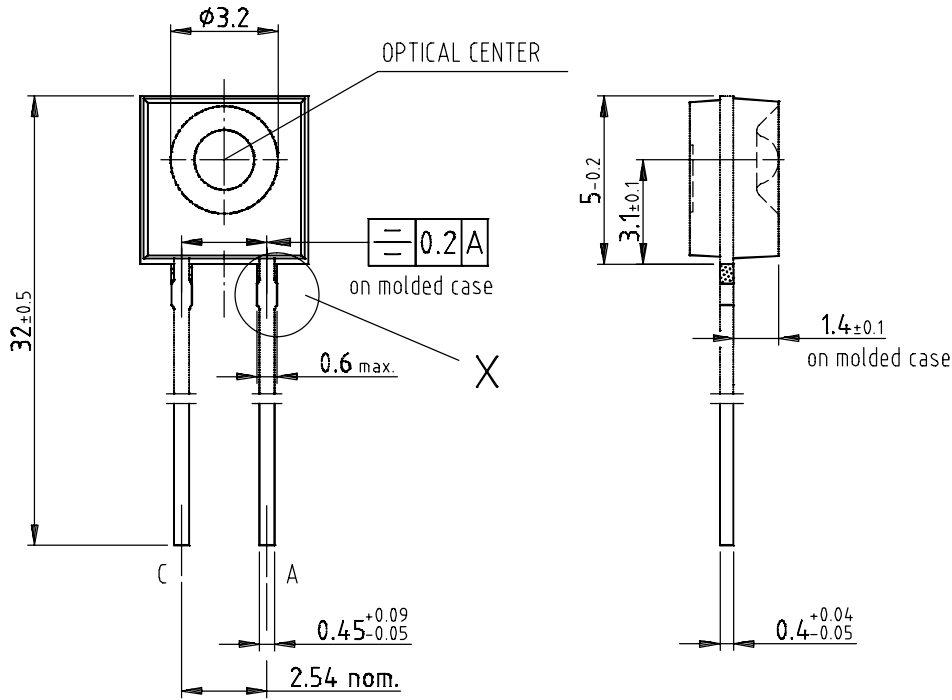
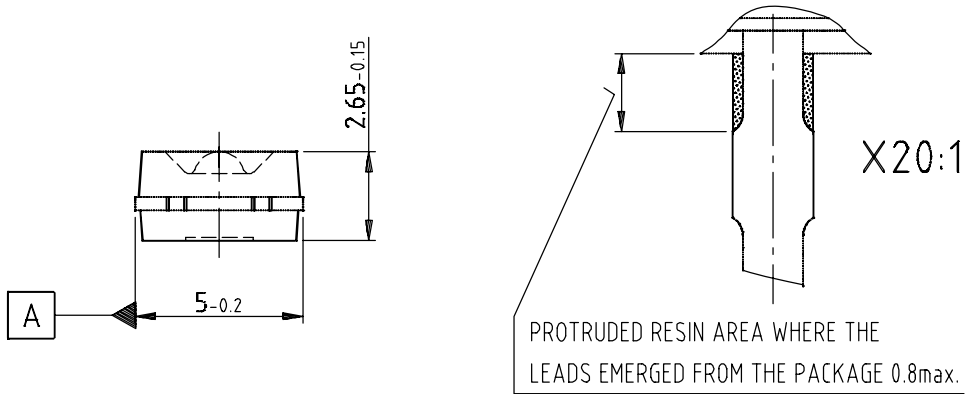
Fig. 7 - Relative Radiant Intensity vs. Ambient Temperature

TSKS5400

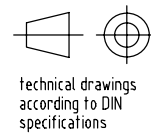
Vishay Semiconductors Infrared Emitting Diode, RoHS Compliant,
950 nm, GaAs



PACKAGE DIMENSIONS in millimeters



LEAD SPACING IS MEASURED WHERE THE
LEADS EMERGED FROM THE PACKAGE



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14345



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